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Front Matter: Volume 11614

, "Front Matter: Volume 11614," Proc. SPIE 11614, Design-Process-Technology Co-optimization XV, 1161401 (7 April 2021); doi: 10.1117/12.2595827

Event: SPIE Advanced Lithography, 2021, Online Only

PROCEEDINGS OF SPIE

Design-Process-Technology Co-optimization XV

**Chi-Min Yuan
Ryoung-Han Kim**
Editors

**22–26 February 2021
Online Only, United States**

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Published by
SPIE

Volume 11614

Proceedings of SPIE 0277-786X, V. 11614

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Design-Process-Technology Co-optimization XV, edited by Chi-Min Yuan, Proc. of SPIE Vol. 11614,
1161401 · © 2021 SPIE · CCC code: 0277-786X/21/\$21 · doi: 10.1117/12.2595827

Proc. of SPIE Vol. 11614 1161401-1

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Author(s), "Title of Paper," in *Design-Process-Technology Co-optimization XV*, edited by Chi-Min Yuan, Ryoung-Han Kim, Proceedings of SPIE Vol. 11614 (SPIE, Bellingham, WA, 2021) Seven-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510640610
ISBN: 9781510640627 (electronic)

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org
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